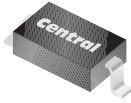


CMDD6001

**SURFACE MOUNT
LOW LEAKAGE SILICON
SWITCHING DIODE**

SUPERmini™



SOD-323 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMDD6001 type is a silicon switching diode manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for switching applications requiring a extremely low leakage diode.

MARKING CODE: C61

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R
 V_{RRM}
 I_F
 I_{FRM}
 I_{FSM}
 I_{FSM}
 P_D
 T_J, T_{stg}
 Θ_{JA}

75
100
250
250
4.0
1.0
250
-65 to +150
500

UNITS

V
V
mA
mA
A
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

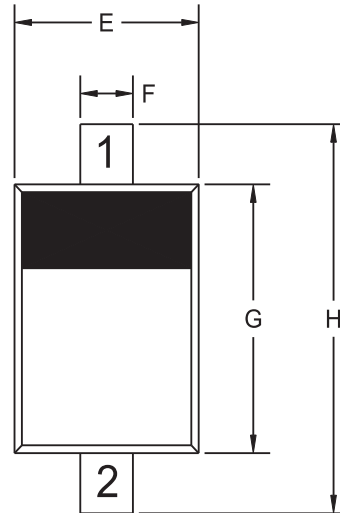
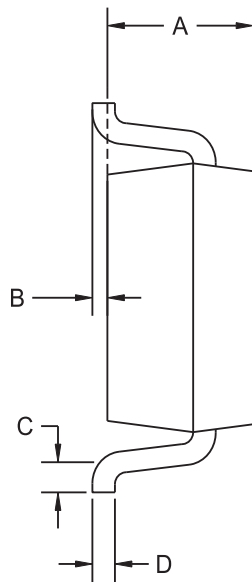
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=75\text{V}$		500	pA
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=1.0\text{mA}$		0.85	V
V_F	$I_F=10\text{mA}$		0.95	V
V_F	$I_F=100\text{mA}$		1.1	V
C_T	$V_R=0, f=1.0\text{MHz}$		2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		3.0	μs

CMDD6001

SURFACE MOUNT
LOW LEAKAGE SILICON
SWITCHING DIODE



SOD-323 CASE - MECHANICAL OUTLINE



R4

LEAD CODE:

- 1) CATHODE
- 2) ANODE

MARKING CODE: C61

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.031	0.039	0.80	1.00
B	0.000	0.004	0.00	0.10
C	0.008	-	0.20	-
D	0.004	0.007	0.11	0.19
E	0.045	0.053	1.15	1.35
F	-	0.014	-	0.35
G	0.063	0.071	1.60	1.80
H	0.094	0.102	2.40	2.60

SOD-323 (REV: R4)

R4 (8-January 2010)